

Supporting Information

High thermal stability Ohmic contact for GaN-based devices

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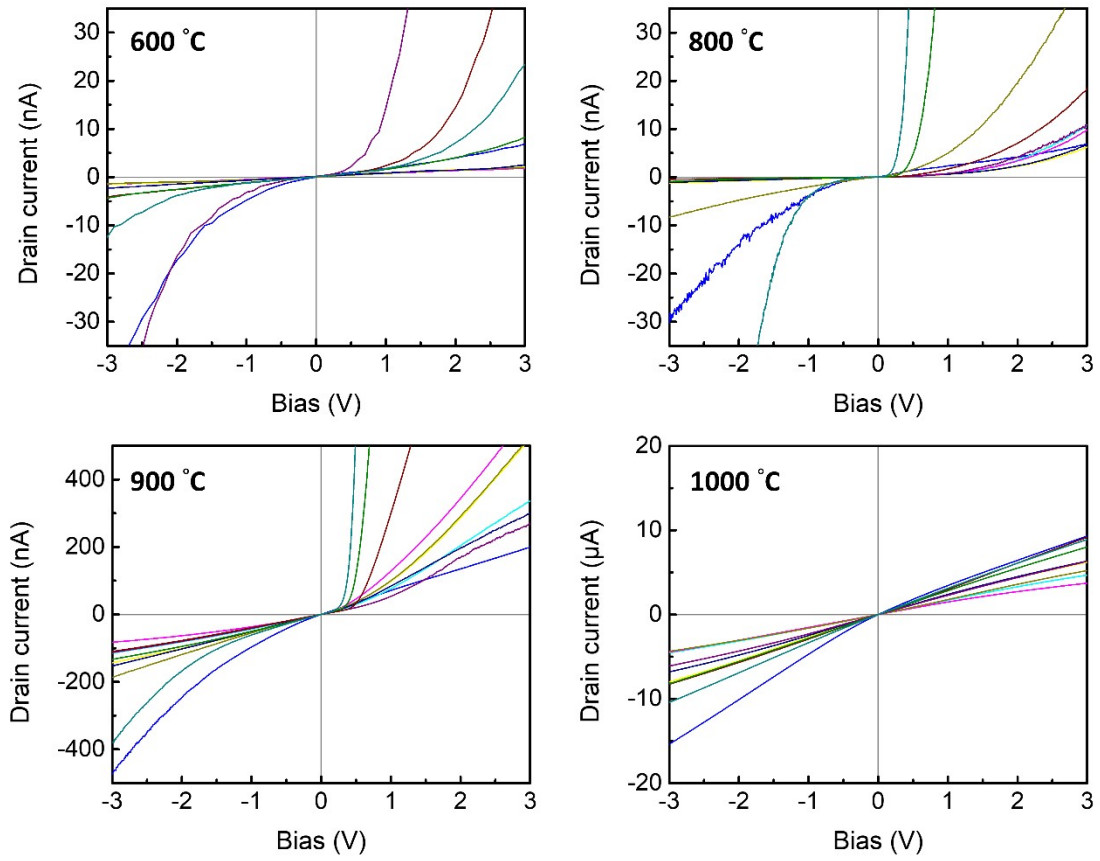


Fig. S1 I-V characteristics of AlGaIn/GaN HEMTs using TiN as contact metal after lower temperature annealing treatments.